

#### NPN power Darlington transistor

#### **Features**

- Good h<sub>FE</sub> linearity
- High f<sub>T</sub> frequency
- Monolithic Darlington configuration with integrated antiparallel collector-emitter diode

#### **Application**

■ Linear and switching industrial equipment

#### **Description**

The device is manufactured in planar technology with "base island" layout and monolithic Darlington configuration.

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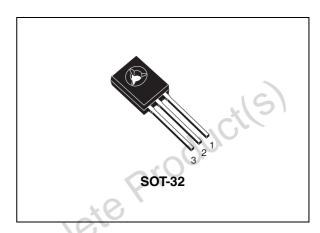


Figure 1. Internal schematic diagram

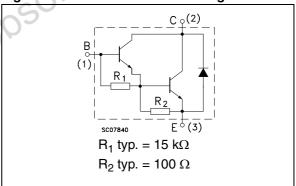


Table 1. Device summary

Order code	Marking	Package	Packaging
MJE802	MJE802	SOT-32	Tube

# 1 Absolute maximum ratings

Table 2. Absolute maximum ratings

$\begin{tabular}{ll} \textbf{Parameter} \\ \hline \textbf{Collector-base voltage } (\textbf{I}_{E}=0) \\ \hline \textbf{Collector-emitter voltage } (\textbf{I}_{B}=0) \\ \hline \textbf{Emitter-base voltage } (\textbf{I}_{C}=0) \\ \hline \textbf{Collector current} \\ \hline \textbf{Collector peak current} \\ \hline \textbf{Base current} \\ \hline \textbf{Total dissipation at } \textbf{T}_{case} = 25 \ ^{\circ}\textbf{C} \\ \hline \end{tabular}$	Value       80       5       4       8       0.1	V V A A A
Collector-emitter voltage (I <sub>B</sub> = 0)  Emitter-base voltage (I <sub>C</sub> = 0)  Collector current  Collector peak current  Base current	5 4 8	V A A
Emitter-base voltage (I <sub>C</sub> = 0)  Collector current  Collector peak current  Base current	5 4 8	V A A
Collector current  Collector peak current  Base current	4 8	A
Collector peak current  Base current	8	Α
Base current	4	
	0.1	Δ.
Total dissipation at T <sub>case</sub> = 25 °C		7 A
	40	W
Storage temperature	-65 to 150	°C
Max. operating junction temperature	150	°C
oduci(s)		
	Max. operating junction temperature	Max. operating junction temperature 150

#### 2 Electrical characteristics

 $T_{case}$  = 25 °C; unless otherwise specified.

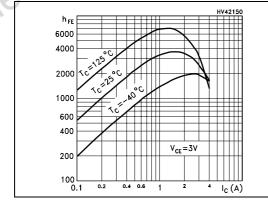
Table 3. Electrical characteristics

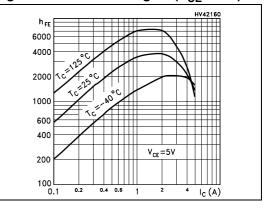
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 80 V V <sub>CB</sub> = 80 V, T <sub>C</sub> = 125 °C		-	0.1 0.5	mA
I <sub>CEO</sub>	Collector cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 80 V		-	0.1	mA
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V		-	2	mA
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA	80	70		V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_C = 1.5 \text{ A}$ $I_B = 30 \text{ mA}$ $I_C = 4 \text{ A}$ $I_B = 40 \text{ mA}$		-	2.5	V
		$I_C = 4 \text{ A}$ $I_B = 40 \text{ H/A}$ $I_C = 1.5 \text{ A}$ $V_{CE} = 3 \text{ V}$		_	2.5	
V <sub>BE(on)</sub> Base-emitter on	Base-emitter on voltage	$I_C = 4 \text{ A}$ $V_{CE} = 3 \text{ V}$			3	V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$I_C = 1.5 \text{ A}$ $V_{CE} = 3 \text{ V}$	750	-		
		$I_C = 4 \text{ A}$ $V_{CE} = 3 \text{ V}$	100	-		
h <sub>fe</sub>	Small signal current gain	I <sub>C</sub> = 1.5 A V <sub>CE</sub> = 3 V f = 1 MHz	1	-		

<sup>1.</sup> Pulse test: pulse duration  $300 \le \mu s$ , duty cycle  $\le 2$  %.

## 2.1 Typical characteristic (curves)

Figure 2. DC current gain ( $V_{CE} = 3 \text{ V}$ ) Figure 3. DC current gain ( $V_{CE} = 5 \text{ V}$ )

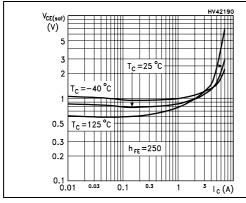




Electrical characteristics MJE802

Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage



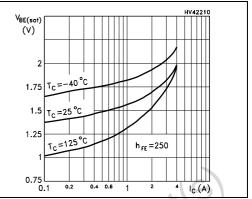
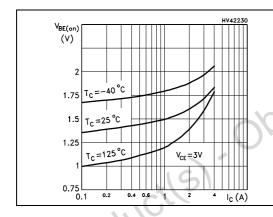


Figure 6. Base-emitter on voltage

Figure 7. Resistive load switching time (on)



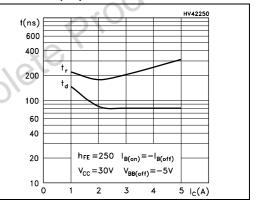
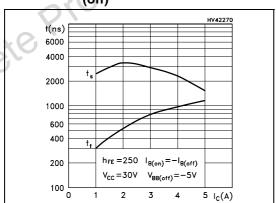


Figure 8. Resistive load switching time (off)



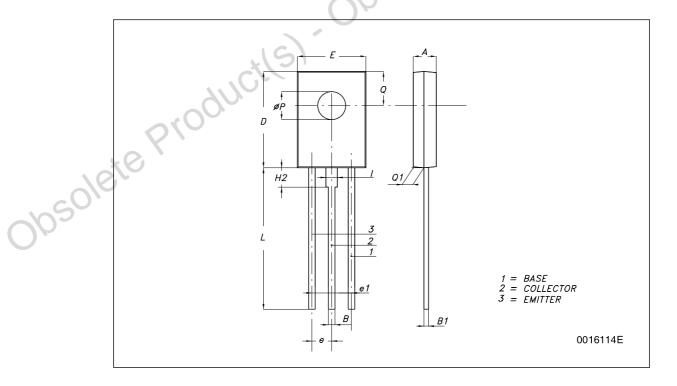
### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Obsolete Product(s). Obsolete Product(s)

#### **SOT-32 (TO-126) MECHANICAL DATA**

DIM.		mm.			
DIWI.	MIN.	TYP	MAX.		
Α	2.4		2.9		
В	0.64		0.88		
B1	0.39		0.63		
D	10.5		11.05		
E	7.4		7.8		
е	2.04	2.29	2.54		
e1	4.07	4.58	5.08		
L	15.3		16		
Р	2.9		3.2		
Q		3.8	(0-		
Q1	1		1.52		
H2		2.15			
1		1.27			



MJE802 Revision history

## 4 Revision history

Table 4. Document revision history

Date	Revision	Changes
21-Jun-2004	3	Document migration, no content change.
28-Aug-2009	4	Modified SOT-32 mechanical data.

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